Docket No.: H0002769
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Hoki Kwon

Application No.: 10/078,474

Filed: February 21, 2002

For: GAAS/AL(GA)AS DISTRIBUTED BRAGG REFLECTOR ON INP

Customer No.: 000128

Confirmation No.: 4800

Art Unit: 2828

Examiner: Dung T. Nguyen

INFORMATION DISCLOSURE STATEMENT (IDS)

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Pursuant to 37 CFR 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO/SB/08. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is filed more than three months after the U.S. filing date, OR more than three months after the date of entry of the national stage of a PCT application, AND after the mailing date of the first Office Action on the merits, whichever occurs first, but before the mailing date of a Final Office Action or Notice of Allowance (37 CFR 1.97(c)).

A copy of each non US patent references on the PTO/SB/08 is attached.

In accordance with 37 CFR 1.97(g), the filing of this Information Disclosure Statement shall not be construed to mean that a search has been made or that no other material information as defined in 37 CFR 1.56(a) exists. In accordance with 37 CFR 1.97(h), the filing

of this Information Disclosure statement shall not be construed to be an admission that any patent, publication or other information referred to therein is "prior art" for this invention unless specifically designated as such.

It is submitted that the Information Disclosure Statement is in compliance with 37 CFR 1.98 and the Examiner is respectfully requested to consider the listed references.

Our check in the amount of $180.00 covering the fee set forth in 37 CFR 1.17(p) is enclosed. The Director is hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 01-1125, under Order No. H0002769. A duplicate copy of this paper is enclosed.

Dated: February 6, 2004

Respectfully submitted,

By _____ #42,766
for Song K. Jung
Registration No.: 35,210
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1900 K Street, N.W.
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PTO/SB/08A (04-03)
Approved for use 04-30-2003. OMB 0651-0031

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet	1	Of	8

COMPLETE IF KNOWN

Application Number	10/078,474
Filing Date	2-21-02
First Named Inventor	Ho Ki Kwon
Art Unit	2828
Examiner Name	Dung T. Nguyen
Attorney Docket Number	H0002769

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No[1]	Document Number Number	Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear
		US 4445218		04-24-1984	Coldren	
		US 4608697		08-26-1986	Coldren	
		US 4622672		11-11-1986	Coldren et al.	
		US 4829347		05-09-1989	Cheng et al.	
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Examiner Signature		Date Considered	

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Sheet	2	Of	8

COMPLETE IF KNOWN	
Application Number	10/078,474
Filing Date	2-21-02
First Named Inventor	Ho Ki Kwon
Group Art Unit	2828
Examiner Name	Dung T. Nguyen
Attorney Docket Number	H0002769

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Sheet	3	Of	8

COMPLETE IF KNOWN	
Application Number	10/078,474
Filing Date	2-21-02
First Named Inventor	Ho Ki Kwon
Group Art Unit	2828
Examiner Name	Dung T. Nguyen
Attorney Docket Number	H0002769

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		US 2003/0157739	A1	08-21-2003	Jiang et al.	
		US 2003/0231680	A1	12-18-2003	Dariusz Burak	

Examiner Signature		Date Considered	

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Sheet	4	Of	8

COMPLETE IF KNOWN	
Application Number	10/078,474
Filing Date	2-21-02
First Named Inventor	Ho Ki Kwon
Group Art Unit	2828
Examiner Name	Dung T. Nguyen
Attorney Docket Number	H0002769

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No[1]	Foreign Patent Document: Country Code[3]	Number[4]	Kind Code[5] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear	T[6]
	✓	EP	0 740 377	A1	10-30-1996	Hewlett-Packard Company		
	✓	EP	0 740 377	B	10-30-1996	Hewlett-Packard Company		
	✓	EP	0 765 014	A1	03-26-1997	France Telecom		
	✓	EP	0 765 014	B1	07-28-1999	France Telecom		
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	✓	EP	0 999 621	B1	11-04-1999	Jayaraman et al.		
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	✓	WO	00/033433	A2	06-08-2000	Arizona Board of Regents		
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	✓	WO	00/038287	A1	06-29-2000	Honeywell, Inc.		
	✓	WO	00/052789	A2	02-29-2000	The Regents of the University of California		
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	✓	WO	00/065700	A2	11-02-2000	Gore Enterprise Holdings, Inc.		
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	✓	WO	01/016642	A2	03-08-2001	Agility Communications		
	✓	WO	01/016642	A3	03-08-2001	Agility Communications		
	✓	WO	01/017076	A2	03-08-2001	The Regents of the University of California		

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Sheet	5	Of	8

COMPLETE IF KNOWN	
Application Number	10/078,474
Filing Date	2-21-02
First Named Inventor	Ho Ki Kwon
Group Art Unit	2828
Examiner Name	Dung T. Nguyen
Attorney Docket Number	H0002769

	✓	WO	01/017076	A3	03-08-2001	The Regents of the University of California		
	✓	WO	01/018919	A1	03-15-2001	The Regents of the University of California		
	✓	WO	01/024328	A2	04-05-2001	Agility Communications		
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	✓	WO	01/033677	A2	05-10-2001	Arizona Board of Regents		
	✓	WO	01/033677	A3	05-10-2001	Arizona Board of Regents		
	✓	WO	01/052373	A2	07-19-2001	Infineon Technologies Ag		
	✓	WO	01/052373	A3	07-19-2001	Infineon Technologies Ag		
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	✓	WO	01/093387	A3	12-06-2001	Sandia Corporation		
	✓	WO	01/095444	A2	12-13-2001	Agility Communications, Inc.		
	✓	WO	01/098756	A2	12-27-2001	The Regents of the University of California		
	✓	WO	02/003515	A2	01-10-2002	Agility Communications, Inc.		
	✓	WO	02/017445	A1	02-28-2002	The Regents of the University of California		
	✓	WO	02/084829	A1	10-24-2002	Cielo Communications, Inc.		
	✓	WO	03/052797	A1	06-26-2003	Jiang et al.		

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T[2]
	✓	International Search Report, dated 08-09-2003, relative to PCT application No. PCT/US 03/05368, the foreign equivalent to the instant U.S. application 10/078,474	
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Application Number	10/078,474
Filing Date	2-21-02
First Named Inventor	Ho Ki Kwon
Group Art Unit	2828
Examiner Name	Dung T. Nguyen
Attorney Docket Number	H0002769

		✓ BLACK, K., et al. "Double-fused 1.5 μm vertical cavity lasers with record high T_o of 132K at room temperature", article, Oct 1, 1998, pgs 1947-9, Vol. 34, No. 20, Electronics Letters.	
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First Named Inventor	Ho Ki Kwon
Group Art Unit	2828
Examiner Name	Dung T. Nguyen
Attorney Docket Number	H0002769

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